

FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP
(Rev. 5/92) 225 Franklin Street, Boston, MA 02110
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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

ATTORNEY DOCKET NO.5342B

Eugene A. Fitzgerald
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EXAMINER

100-66 U.S. PTO
1019/761497
01/16/01

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TTN	AA	5,208,182	5/4/93	Narayan et al.	438	509	11/12/91
TTN	AB	5,252,173	10/12/93	Inoue	438	509	11/22/91
TTN	AC	5,279,687	01/18/94	Tuppen et al.	148	33.2	02/27/90
TTN	AD	6,117,750	09/12/00	Bensahel et al.	438	478	12/21/98
TTN	AE	5,210,052	05/11/93	Takasaki	438	509	05/13/92
TTN	AF	5,221,413	06/22/93	Brasen et al.	117	89	04/24/91
TTN	AG	5,308,444	05/03/94	Fitzgerald, Jr. et al.	117	90	05/28/93
TTN	AH	5,442,205	08/15/95	Brasen et al.	257	191	09/09/93
TTN	AI	5,810,924	09/22/98	Legoues et al.	117	89	06/07/95
TTN	AJ	6,107,653	08/22/00	Fitzgerald	257	191	06/23/98

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
TTN	AK	63073398	3/29/88	Japan		—	yes (abstract)
	AL						
	AM						
	AN						
	AO						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
TTN	AP	"Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si"; by Fitzgerald et al. 1992 American Vacuum society; pages 1807-1819
TTN	AQ	"GeSi/Si NANOSTRUCTURES" by E.A. Fitzgerald; Department of Materials Science, Massachusetts Institute of Technology (1995) pgs; 1-15

EXAMINER *Chalyan*DATE CONSIDERED *01/31/2002*

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Eugene A. Fitzgerald
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2812
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01/16/2001
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TN	AA	4,900,372	02/13/1990	Lee et al.	148	33.4	03/02/1989
	AB						
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	AD						
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	AG						
	AH						
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	AK						
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AP	Hsin-Chiao Luan et al., "High-quality Ge epilayers on Si with low threading-dislocation densities," <i>Applied Physics Letters</i> , American Institute of Physics, New York, Vol. 75, No. 19, November 8, 1999, pages 2909-2911.
	AQ	

EXAMINER	<i>Eugene Fitzgerald</i>	DATE CONSIDERED
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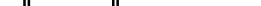
U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DEPARTMENT	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
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	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AK						
	AL						
	AM						
	AN						
	AO						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
TTW	AP	G. Kissinger et al., "Stepwise Equilibrated Graded Ge_xSi_{1-x} Buffer With Very Low Threading Dislocation Density on Si(001)," <i>Applied Physics Letters</i> 66 (16), April 17, 1995, of the 1995 American Institute of Physics Literature, pages 2083-2085.
	AQ	
EXAMINER		
	DATE CONSIDERED 	

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